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November 2013

### FQL40N50F

## N-Channel QFET® FRFET® MOSFET 500 V, 40 A, 110 mΩ

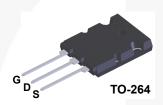
### **Description**

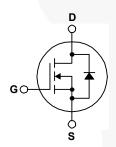
This N-Channel enhancement mode power MOSFET is • 40 A, 500 V,  $R_{DS(on)}$  = 110 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 155 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 95 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

### **Features**

- $I_D = 20 A$

- · Fast Recovery Body Diode (Max. 250 ns)





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FQL40N50F	Unit
V <sub>DSS</sub>	Drain-Source Voltage	500	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)	40	Α
	- Continuous (T <sub>C</sub> = 100°C)	25	Α
I <sub>DM</sub>	Drain Current - Pulsed (N	ote 1) 160	Α
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (N	ote 2) 1800	mJ
I <sub>AR</sub>	Avalanche Current (N	ote 1) 40	Α
E <sub>AR</sub>	Repetitive Avalanche Energy (N	ote 1) 46	mJ
dv/dt	Peak Diode Recovery dv/dt (N	ote 3) 20	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)	460	W
	- Derate above 25°C	3.7	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.	300	°C

### **Thermal Characteristics**

Symbol	Parameter	FQL40N50F	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.27	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	30	°C/W	

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQL40N50F	FQL40N50F	TO-264	Tube	N/A	N/A	25 units

Symbol	Parameter	Test Conditions		Тур.	Max.	Unit
Off Cha	racteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	500			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.48		V/°(
I <sub>DSS</sub>	Zana Oata Waltana Basia Oussant	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V			50	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C			500	μА
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	vo eteriotico					
V <sub>GS(th)</sub>	racteristics Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.085	0.11	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 20 A		29		S
Dynam C <sub>iss</sub>	ic Characteristics Input Capacitance	1		5800	7500	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V, } V_{GS} = 0 \text{ V,}$ f = 1.0  MHz		880	1150	рF
C <sub>rss</sub>	Reverse Transfer Capacitance			95	120	рF
				00	120	Pi
t <sub>d(on)</sub>	ng Characteristics Turn-On Delay Time			140	290	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 250 \text{ V}, I_D = 40 \text{ A},$		440	890	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_G = 25 \Omega$		350	700	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		250	500	ns
Q <sub>q</sub>	Total Gate Charge	V = 400 V I = 40 A		155	200	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{DS} = 400 \text{ V}, I_{D} = 40 \text{ A},$ $V_{GS} = 10 \text{ V}$		37		nC
Q <sub>gd</sub>	Gate-Drain Charge	V <sub>GS</sub> = 10 V (Note 4)		78		nC
	ource Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				40	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				160	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 40 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 40 A,		>	250	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> / dt = 100 A/μs		1.3	//	μC

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 2.0 mH, I<sub>AS</sub> = 40 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  40 A, di/dt  $\leq$  200 A/ $\mu$ s , V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature.

### **Typical Characteristics**

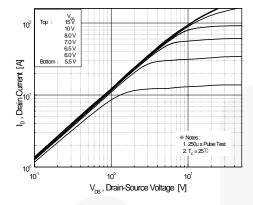


Figure 1. On-Region Characteristics

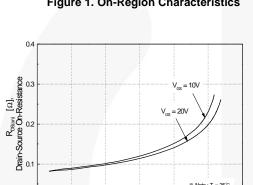


Figure 3. On-Resistance Variation vs **Drain Current and Gate Voltage** 

90

In, Drain Current [A]

30

60

150

180

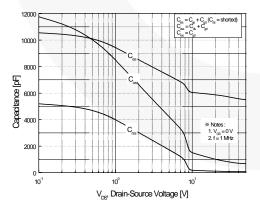


Figure 5. Capacitance Characteristics

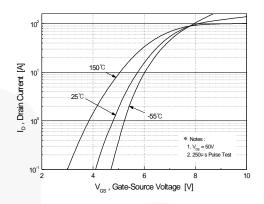


Figure 2. Transfer Characteristics

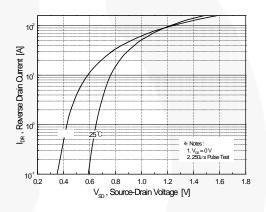


Figure 4. Body Diode Forward Voltage **Variation with Source Current** and Temperature

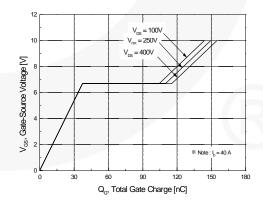


Figure 6. Gate Charge Characteristics

# (Dezignation) 1.0 (Dezignation)

Typical Characteristics (Continued)

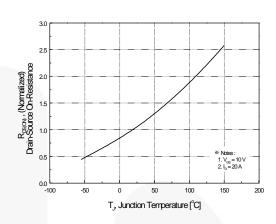
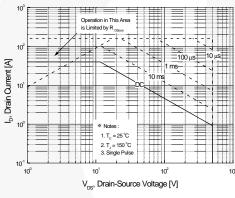


Figure 8. On-Resistance Variation vs Temperature



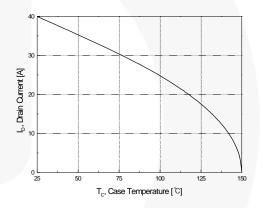


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs Case Temperature

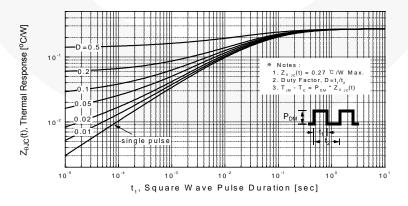


Figure 11. Transient Thermal Response Curve

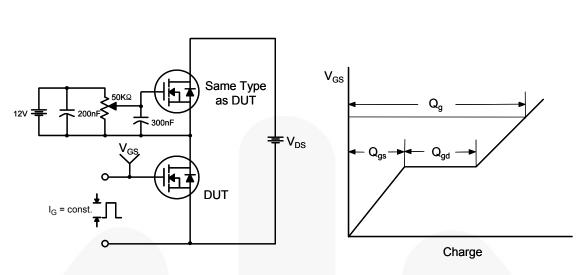


Figure 12. Gate Charge Test Circuit & Waveform

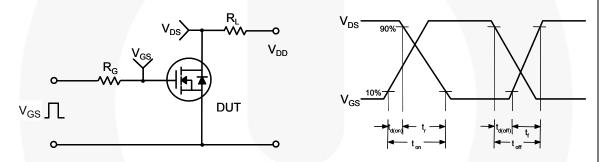


Figure 13. Resistive Switching Test Circuit & Waveforms

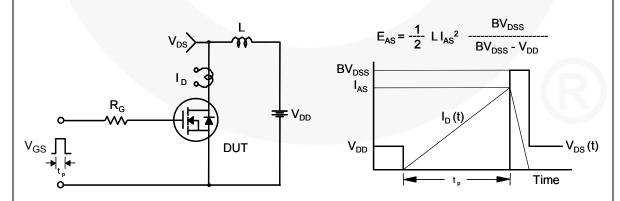
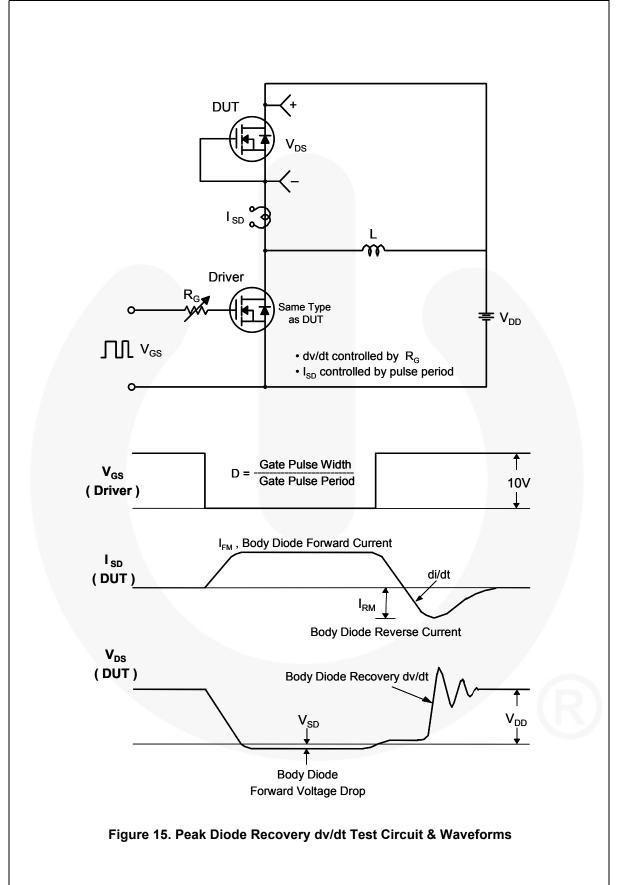
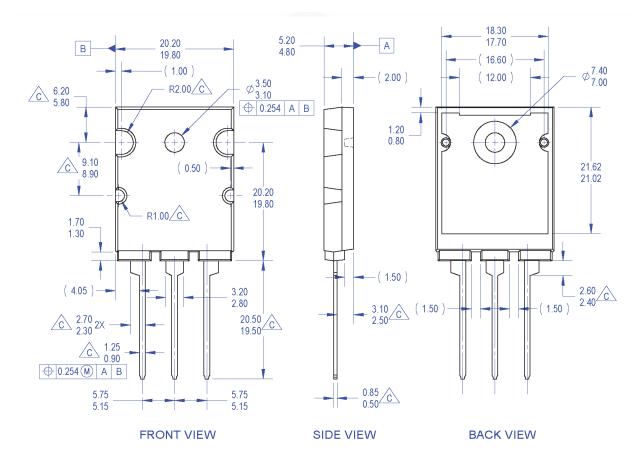
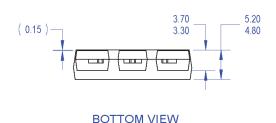


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**





### NOTES:

- A. PACKAGE REFERENCE: JEDEC TO264 VARIATION AA
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- OUT OF JEDEC STANDARD VALUE.
  DIMENSION AND TOLERANCE AS PER ASME
  Y14.5-1994.
- E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS. F. THIS PACKAGE IS INTENDED ONLY FOR "FS PKG CODE AR"
- G. DRAWING FILE NAME: TO264A03REV1

Figure 16. TO264, Molded, 3-Lead, Jedec Variation AA

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